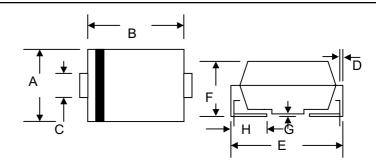
# **SEMICONDUCTOR**

### 1.0A SURFACE MOUNT GLASS PASSIVATED RECTIFIER

## Data Sheet 2558 Rev.—

### **Features**

- Glass Passivated Die Construction
- Ideally Suited for Automatic Assembly
- Low Forward Voltage Drop
- Surge Overload Rating to 30A Peak
- Low Power Loss
- Built-in Strain Relief
- Plastic Case Material has UL Flammability Classification Rating 94V-O



### **Mechanical Data**

Case: Molded Plastic

 Terminals: Solder Plated, Solderable per MIL-STD-750, Method 2026

Polarity: Cathode Band or Cathode Notch

Marking: Type Number

• Weight: 0.064 grams (approx.)

SMA/DO-214AC							
Dim	Min Max						
Α	0.098(2.50)	0.114(2.90)					
В	0.157(4.00)	0.181(4.60)					
С	0.055(1.40)	0.063(1.60)					
D	0.006(0.15)	0.012(0.31)					
E	0.189(4.80)	0.208(5.28)					
F	0.079(2.00)	0.096(2.44)					
G	0.002(0.05)	0.008(0.20)					
Н	0.030(0.76)	0.060(1.52)					
All Dimensions in inch(mm)							

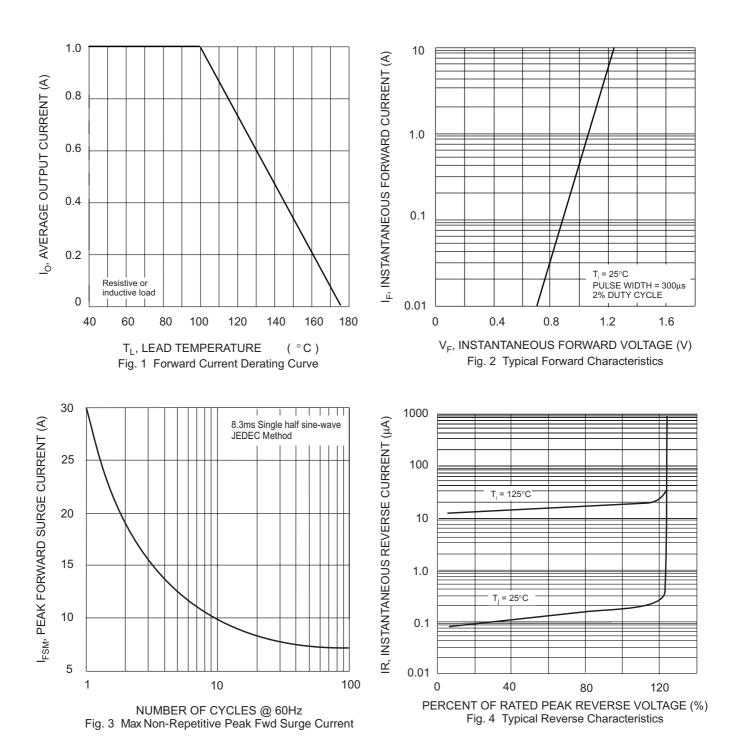
## Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Characteristic		Symbol	S1A	S1B	S1D	S1G	S1J	S1K	S1M	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		Vrrm Vrwm Vr	50	100	200	400	600	800	1000	٧
RMS Reverse Voltage		VR(RMS)	35	70	140	280	420	560	700	V
Average Rectified Output Current @T <sub>L</sub> = 100°C		lo	1.0							Α
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)		IFSM	30							Α
Forward Voltage	@I <sub>F</sub> = 1.0A	VFM	1.10						V	
Peak Reverse Current At Rated DC Blocking Voltage	@T <sub>A</sub> = 25°C @T <sub>A</sub> = 125°C	IRM	5.0 200					μA		
Reverse Recovery Time (Note 1)		trr	2.5							μS
Typical Junction Capacitance (Note 2)		Cı	15							pF
Typical Thermal Resistance (Note 3)		RTHJL	30							°C/W
Operating and Storage Temperature Range		TJ, TSTG	-65 to +175							°C

Note: 1. Measured with  $I_F = 0.5A$ ,  $I_R = 1.0A$ ,  $I_{rr} = 0.25A$ ,

2. Measured at 1.0 MHz and applied reverse voltage of 4.0 V DC.

3. Mounted on P.C. Board with 8.0mm<sup>2</sup> land area.





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